

TOSHIBA TRANSISTOR SILICON NPN TRIPLE DIFFUSED TYPE

2SC5358

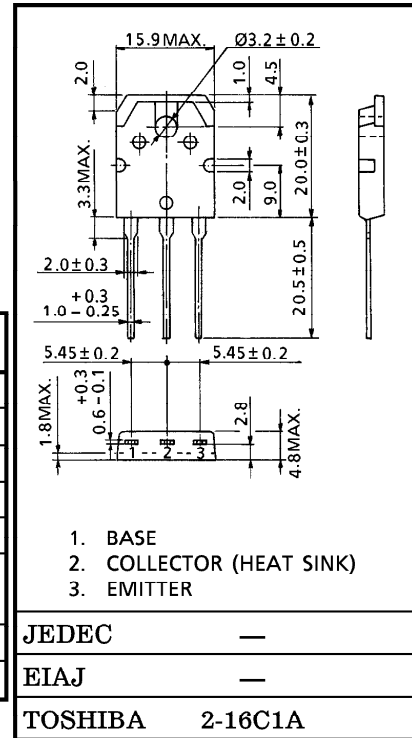
POWER AMPLIFIER APPLICATIONS

Unit in mm

- Complementary to 2SA1986
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	230	V
Collector-Emitter Voltage	V _{CEO}	230	V
Emitter-Base Voltage	V _{EB0}	5	V
Collector Current	I _C	15	A
Base Current	I _B	1.5	A
Collector Power Dissipation (Tc = 25°C)	P _C	150	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



Weight : 4.7g (Typ.)

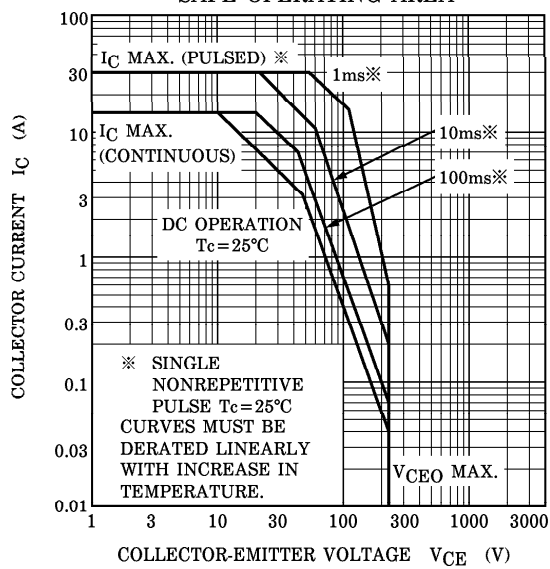
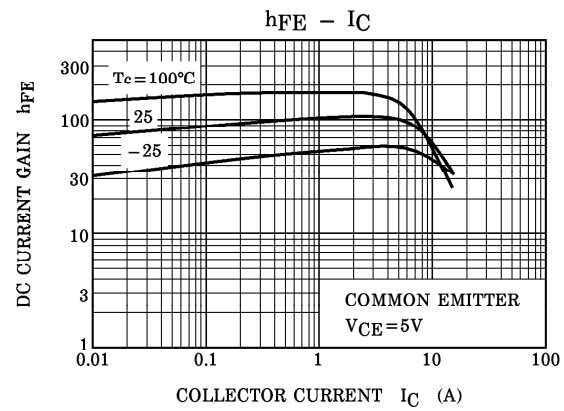
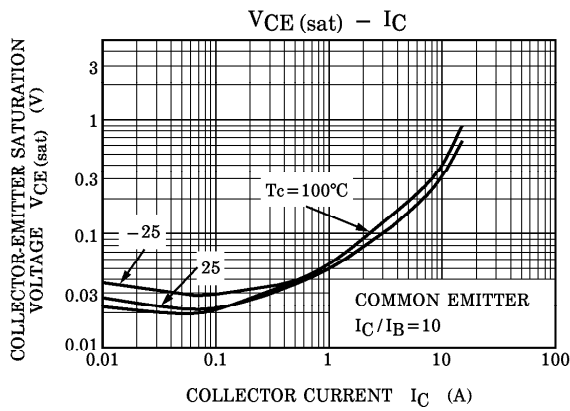
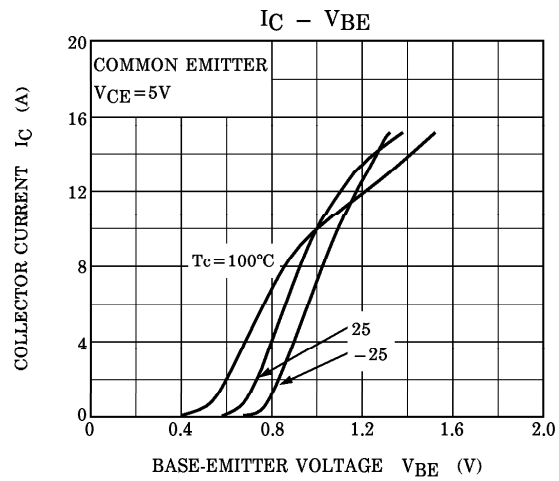
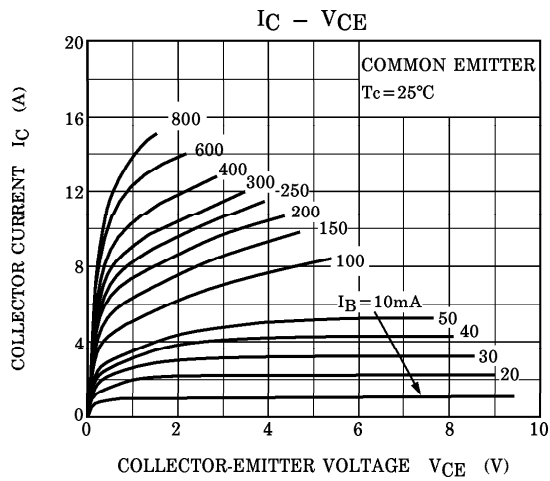
ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CBO}	V _{CB} = 230V, I _E = 0	—	—	5.0	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} = 5V, I _C = 0	—	—	5.0	μA
Collector-Emitter Breakdown Voltage	V (BR) CEO	I _C = 50mA, I _B = 0	230	—	—	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} = 5V, I _C = 1A	55	—	160	—
	h _{FE} (2)	V _{CE} = 5V, I _C = 7A	35	87	—	—
Collector-Emitter Saturation Voltage	V _{CE} (sat)	I _C = 8A, I _B = 0.8A	—	0.4	3.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = 5V, I _C = 7A	—	1.0	1.5	V
Transition Frequency	f _T	V _{CE} = 5V, I _C = 1A	—	30	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = 10V, I _E = 0, f = 1MHz	—	200	—	pF

(Note) h_{FE} (1) Classification R : 55~110, O : 80~160

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TOSHIBA TRANSISTOR SILICON PNP TRIPLE DIFFUSED TYPE

2SA1986

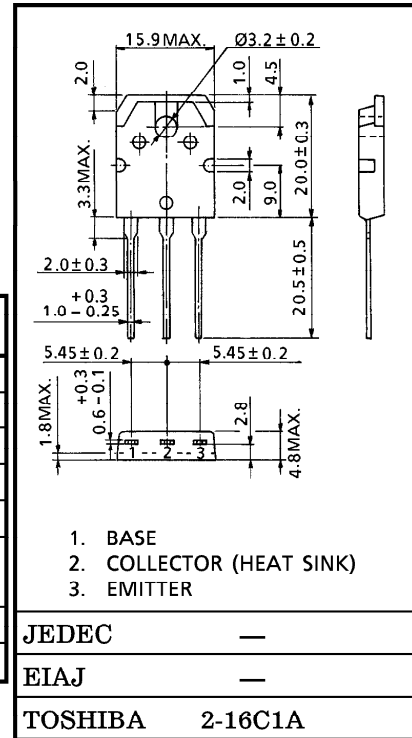
POWER AMPLIFIER APPLICATIONS

Unit in mm

- Complementary to 2SC5358
- Recommend for 80W High Fidelity Audio Frequency Amplifier Output Stage.

MAXIMUM RATINGS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	RATING	UNIT
Collector-Base Voltage	V _{CB0}	-230	V
Collector-Emitter Voltage	V _{CEO}	-230	V
Emitter-Base Voltage	V _{EB0}	-5	V
Collector Current	I _C	-15	A
Base Current	I _B	-1.5	A
Collector Power Dissipation (Tc = 25°C)	P _C	150	W
Junction Temperature	T _j	150	°C
Storage Temperature Range	T _{stg}	-55~150	°C



Weight : 4.7g (Typ.)

ELECTRICAL CHARACTERISTICS (Ta = 25°C)

CHARACTERISTIC	SYMBOL	TEST CONDITION	MIN.	TYP.	MAX.	UNIT
Collector Cut-off Current	I _{CB0}	V _{CB} = -230V, I _E = 0	—	—	-5.0	μA
Emitter Cut-off Current	I _{EB0}	V _{EB} = -5V, I _C = 0	—	—	-5.0	μA
Collector-Emitter Breakdown Voltage	V _{(BR) CEO}	I _C = -50mA, I _B = 0	-230	—	—	V
DC Current Gain	h _{FE} (1) (Note)	V _{CE} = -5V, I _C = -1A	55	—	160	—
	h _{FE} (2)	V _{CE} = -5V, I _C = -7A	35	70	—	—
Collector-Emitter Saturation Voltage	V _{CE (sat)}	I _C = -8A, I _B = -0.8A	—	-1.5	-3.0	V
Base-Emitter Voltage	V _{BE}	V _{CE} = -5V, I _C = -7A	—	-1.0	-1.5	V
Transition Frequency	f _T	V _{CE} = -5V, I _C = -1A	—	30	—	MHz
Collector Output Capacitance	C _{ob}	V _{CB} = -10V, I _E = 0, f = 1MHz	—	360	—	pF

(Note) h_{FE} (1) Classification R : 55~110, O : 80~160

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